Unit in mm

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2 S C 3 6 6 6

### **AUDIO POWER AMPLIFIER APPLICATIONS**

• High DC Current Gain:  $h_{FE(1)}=100\sim320$ 

#### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	30	V
Collector-Emitter Voltage	$v_{CEO}$	30	V
Emitter-Base Voltage	$V_{ m EBO}$	5	V
Collector Current	$I_{\mathbf{C}}$	1	A
Base Current	$I_{\mathbf{B}}$	0.1	A
Collector Power Dissipation	$P_{\mathbf{C}}$	1000	mW
Junction Temperature	$T_{j}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

7.1MAX
3.8
3.2
3.2
0.55-0.05
0.85
0.45-0.05
1. BASE
2. COLLECTOR
3. EMITTER

JEDEC

JEITA

TOSHIBA
2.7MAX
2.7MAX
0.15
0.45-0.05
1.025±0.05

1.025±0.05

TOSHIBA
2.7D101A

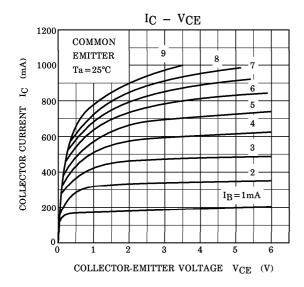
Weight: 0.2g (Typ.)

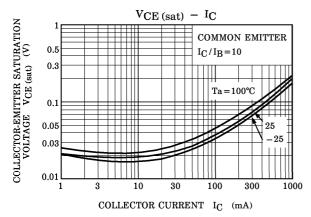
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

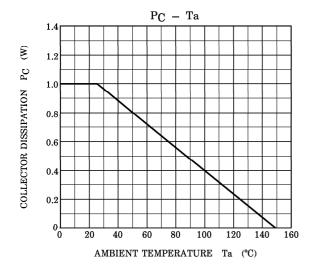
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 30V, I_{E} = 0$	_	_	100	nA
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=5V, I_C=0$	_	_	100	nA
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C} = 10  {\rm mA}, \ I_{\rm B} = 0$	30	_	_	v
DC Current Gain	hFE (1) (Note)	$V_{CE} = 2V, I_{C} = 100 \text{mA}$	100	_	320	
	h <sub>FE (2)</sub>	$V_{CE}=2V, I_{C}=800mA$	40	_	_	
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	$I_{\rm C} = 800  \rm mA$ , $I_{\rm B} = 80  \rm mA$	-	_	0.5	v
Base-Emitter Voltage	$ m v_{BE}$	$V_{CE} = 2V, I_{C} = 800 \text{mA}$	_	0.9	1.5	V
Transition Frequency	$ m f_{T}$	$V_{CE} = 2V, I_{C} = 100 \text{mA}$	_	150	_	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=1MHz$	_	13	_	pF

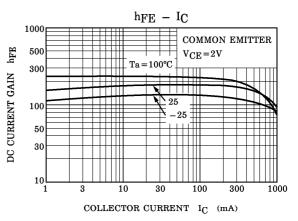
(Note) : hFE Classification  $O:100\sim200$ ,  $Y:160\sim320$ 

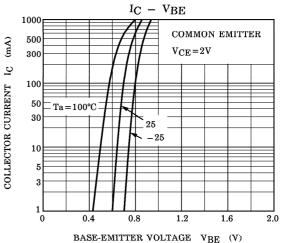
1 2001-11-05

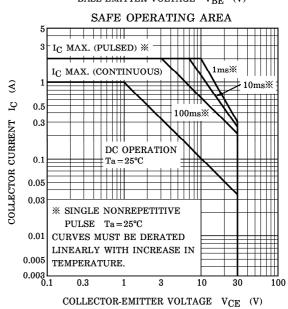












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